

40V 1.8mohm SGT Power MOSFET

AKG40N018G

Description:

This N channel SGT MOSFET has been designed to very low on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, especially for high efficiency power management applications

Features:

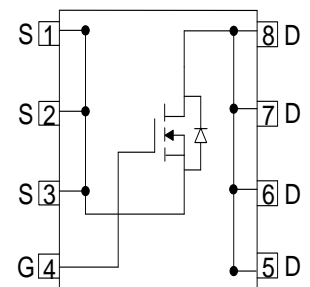
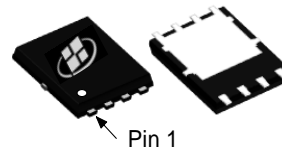
- N-channel, optimized for high-speed smooth switching
- Excellent Gate Charge $\times R_{DS(on)}$ (FOM)
- Very low on-resistance
- RoHS compliant ^(Note 1)
- Halogen-free ^(Note 1)

Applications:

- DC-DC Converter
- Power Tools
- Load Switching

Key Performance Parameters:

| Parameter | Value | Unit |
|------------------------------------|-------|------------|
| V_{DS} | 40 | V |
| $R_{DS(on), max}$ @ $V_{GS} = 10V$ | 1.8 | m Ω |
| I_D | 130 | A |



Ordering Information:

| Ordering Code | Package Type | Marking Code | Form | Packing |
|---------------|--------------|--------------|----------------|---------|
| AKG40N018G | PDFN5X6-8L | G40N018G | 13 Inches Reel | 5000PCS |

Notes:

1. Contact ALKAIDSEMI sales for detail information

Maximum Ratings (T_A = 25°C unless otherwise noted)

| Symbol | Parameter | Value | Units |
|-----------------------------------|--|-------------|-------|
| V _{DS} | Drain-Source Voltage | 40 | V |
| I _D | Drain Current - Continuous (T _C = 25°C) ^(Note 1) | 130 | A |
| | Drain Current - Continuous (T _C = 100°C) | 82 | A |
| I _{DM} | Drain Current - Pulsed ^(Note 2) | 400 | A |
| V _{GS} | Gate-Source Voltage | ± 20 | V |
| E _{AS} | Single Pulsed Avalanche Energy ^(Note 3) | 320 | mJ |
| P _D | Power Dissipation (T _C = 25°C) | 89 | W |
| T _J , T _{STG} | Operating and Storage Temperature Range | -55 to +150 | °C |

Thermal Characteristics

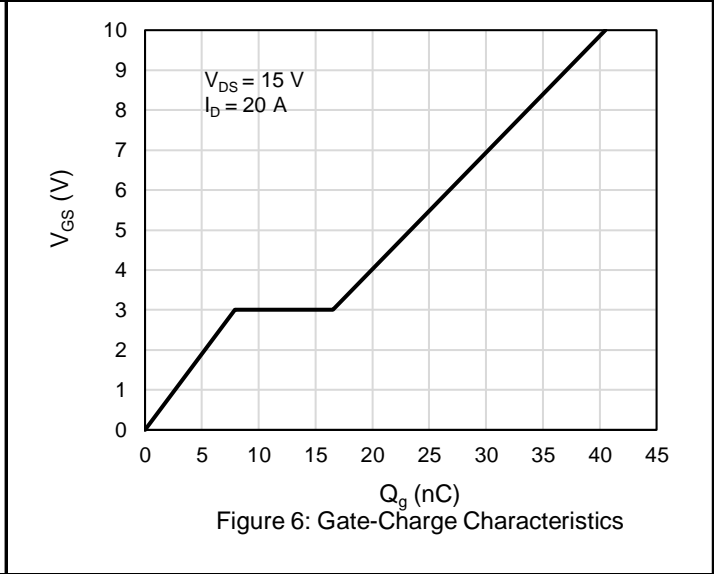
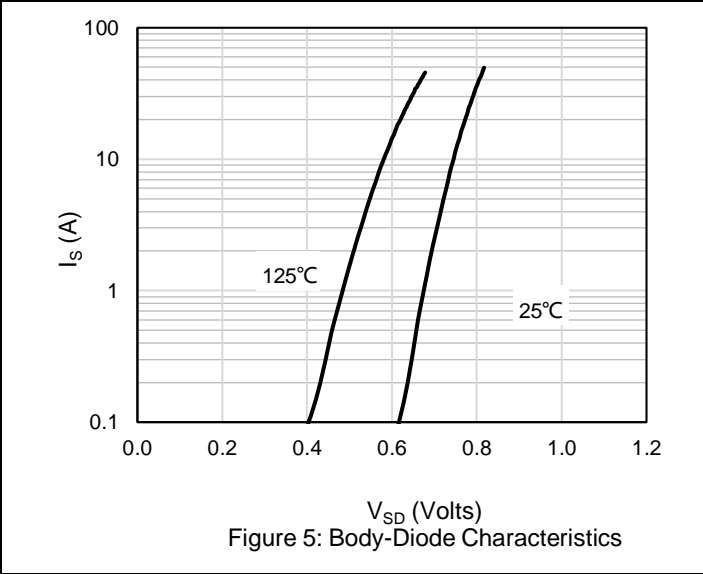
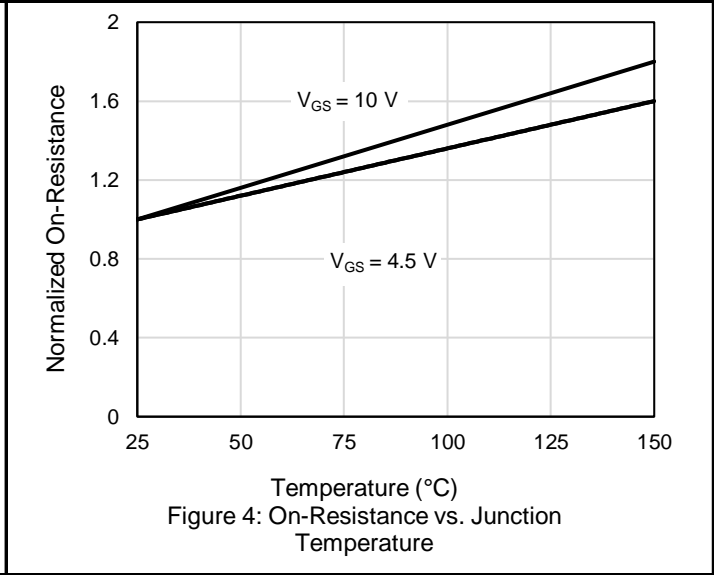
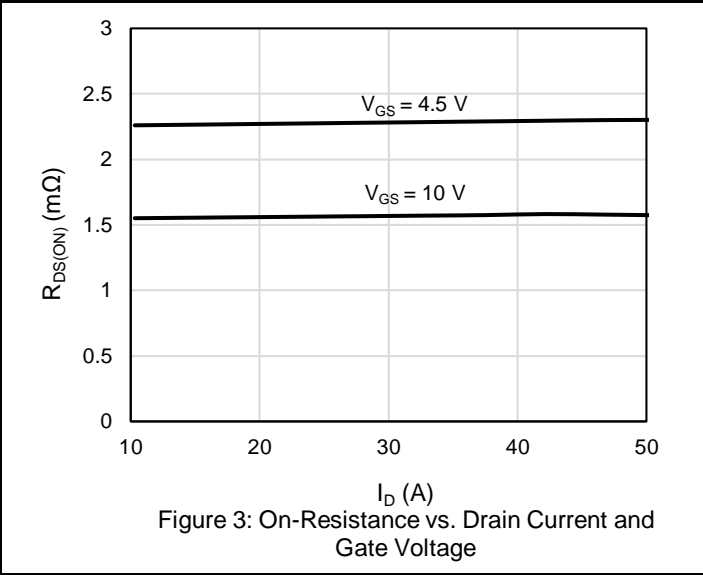
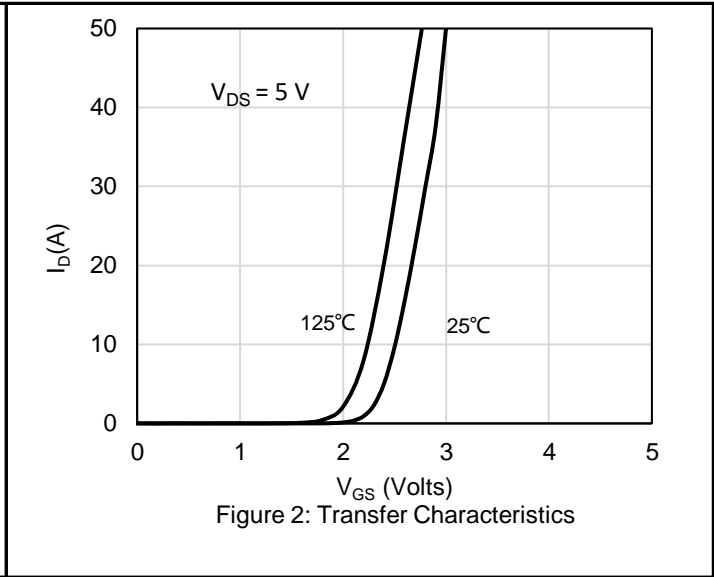
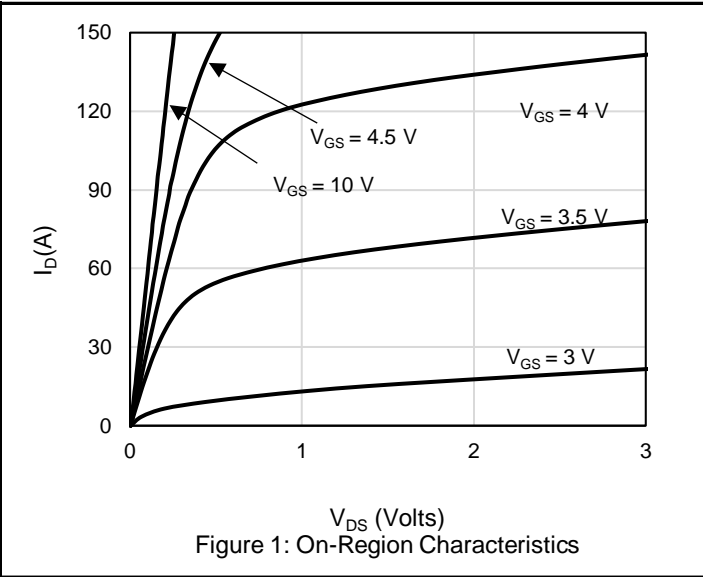
| Symbol | Parameter | Value | Units |
|------------------|---|-------|-------|
| R _{θJC} | Thermal Resistance, Junction-to-Case, Steady-State | 1.4 | °C/W |
| R _{θJA} | Thermal Resistance, Junction-to-Ambient, Steady-State ^(Note 4) | 4.1 | °C/W |

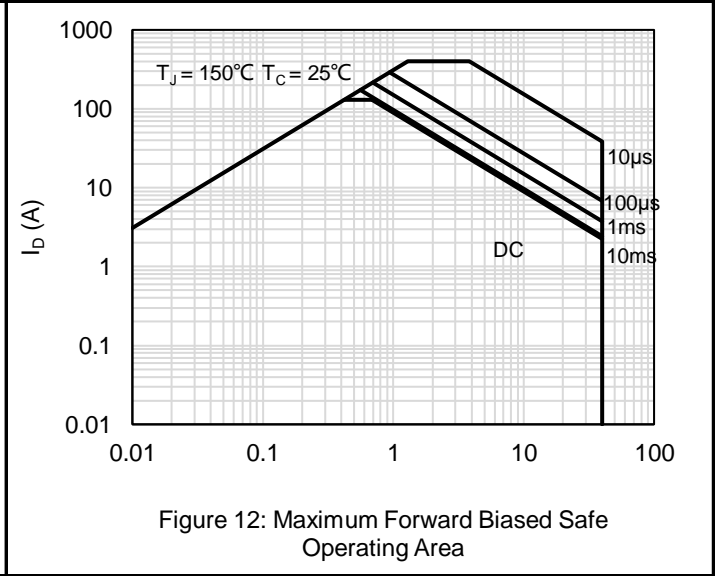
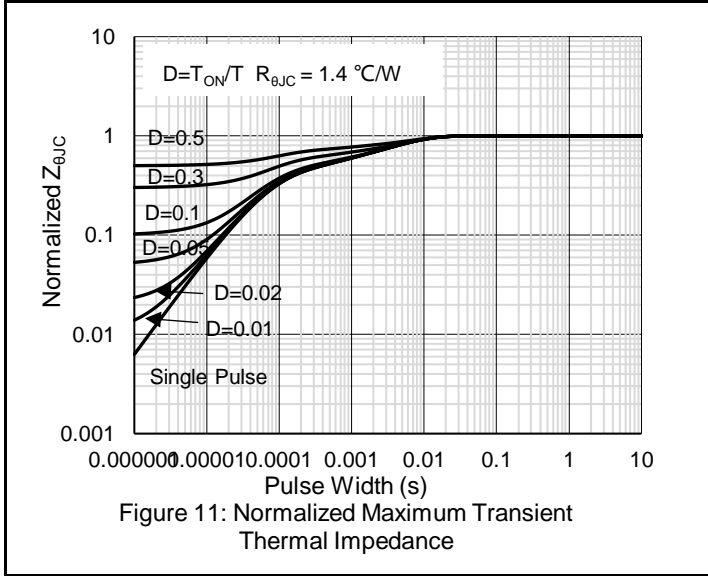
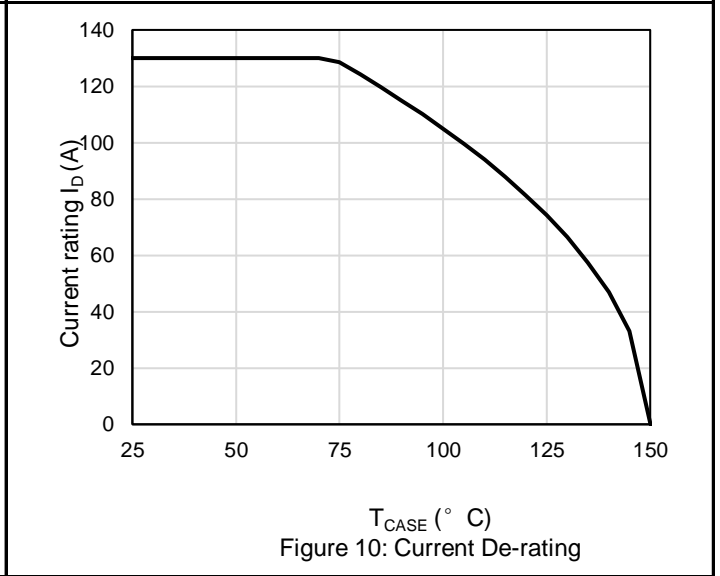
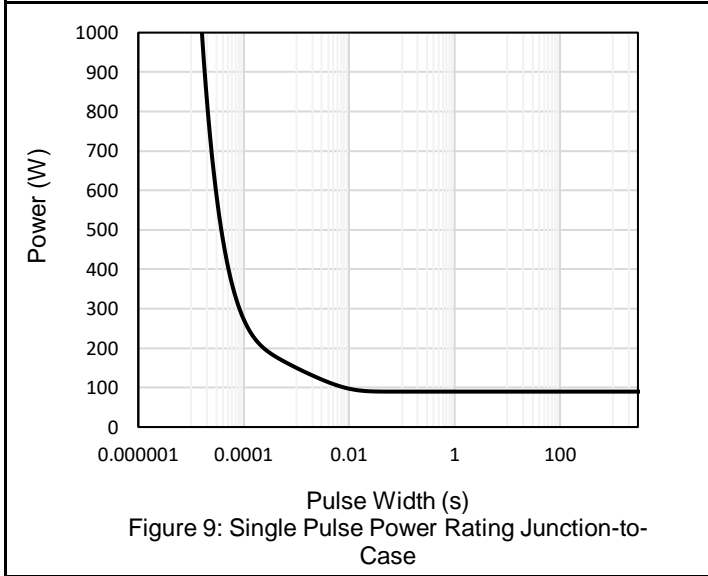
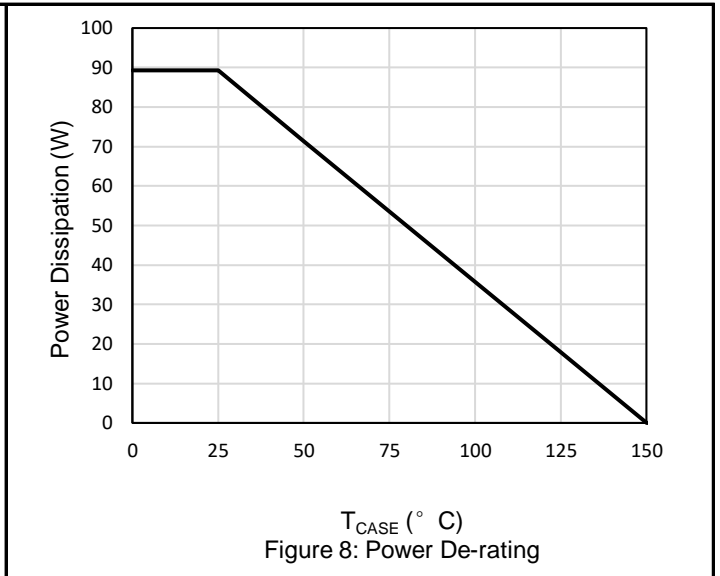
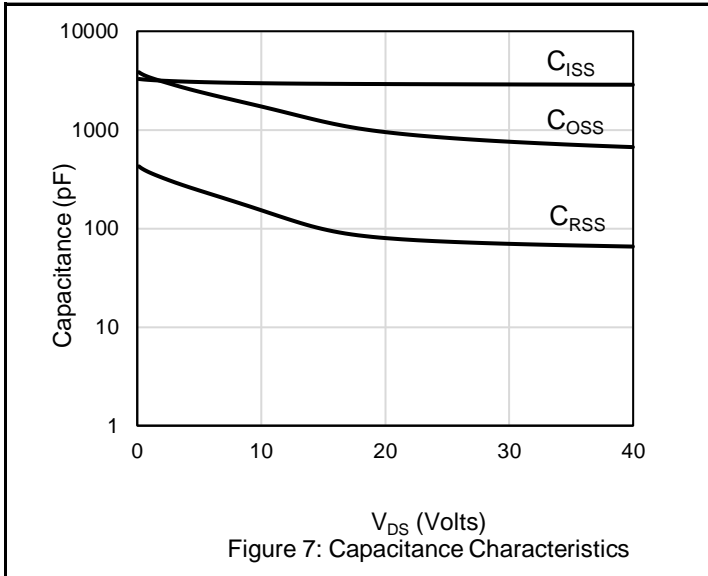
Notes:

1. The max drain current rating is package limited
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. L = 0.5 mH, V_{DD} = 20V, I_{AS} = 35 A, R_G = 50 Ω, Starting T_J = 25 °C
4. Mount on minimum PCB layout

| Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted) | | | | | | |
|--|---|---|-----|------|-----------|---------------|
| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
| Static Characteristics | | | | | | |
| BV_{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$ | 40 | | | V |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V},$ | | | 1 | μA |
| I_{GSS} | Gate Leakage Current | $V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$ | | | ± 100 | nA |
| $V_{GS(TH)}$ | Gate Threshold voltage | $V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$ | 1 | 1.8 | 2.5 | V |
| $R_{DS(ON)}$ | Drain-Source on-state resistance | $V_{GS} = 10\text{ V}, I_D = 20\text{ A}$ | | 1.55 | 1.8 | m Ω |
| | | $V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$ | | 2.3 | 3.3 | |
| Dynamic Characteristics | | | | | | |
| C_{ISS} | Input Capacitance | $V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V},$ $F = 1\text{ MHz}$ | | 2916 | | pF |
| C_{OSS} | Output Capacitance | | | 966 | | pF |
| C_{RSS} | Reverse Transfer Capacitance | | | 81 | | pF |
| R_G | Gate Resistance | $F = 1\text{ MHz}$ | | 6.7 | | Ω |
| Switching Characteristics | | | | | | |
| $T_{D(ON)}$ | Turn On Delay Time | $V_{DD} = 15\text{ V}, I_D = 20\text{ A},$ $V_{GS} = 10\text{ V}, R_G = 3.3\ \Omega$ | | 8.5 | | nS |
| T_R | Rise Time | | | 46.5 | | nS |
| $T_{D(OFF)}$ | Turn Off Delay Time | | | 63.5 | | nS |
| T_F | Fall Time | | | 39 | | nS |
| Q_G | Total Gate Charge | $V_{DD} = 15\text{ V}, I_D = 20\text{ A},$ $V_{GS} = 10\text{ V}$ | | 40.5 | | nC |
| Q_{GS} | Gate-Source Charge | | | 7.9 | | nC |
| Q_{GD} | Gate-Drain Charge | | | 6.6 | | nC |
| Drain-Source Diode Characteristics and Maximum Ratings | | | | | | |
| I_S | Maximum Continuous Body-Diode Forward Current | | | 130 | | A |
| I_{SM} | Maximum Pulsed Body-Diode Forward Current ^(NOTE 2) | | | 400 | | A |
| V_{SD} | Diode Forward Voltage | $V_{GS} = 0\text{ V}, I_S = 1\text{ A}$ | | 0.7 | 1.2 | V |
| T_{RR} | Reverse recovery time | $V_{DD} = 20\text{ V}, I_D = 20\text{ A},$ $di/dt = 100\text{ A}/\mu\text{s}$ | | 39 | | ns |
| Q_{RR} | Reverse recovery charge | | | 30 | | nC |

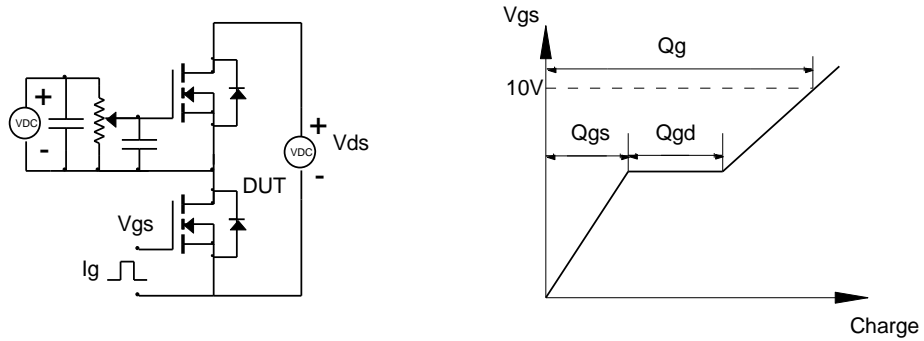
Electrical Characteristics Diagrams



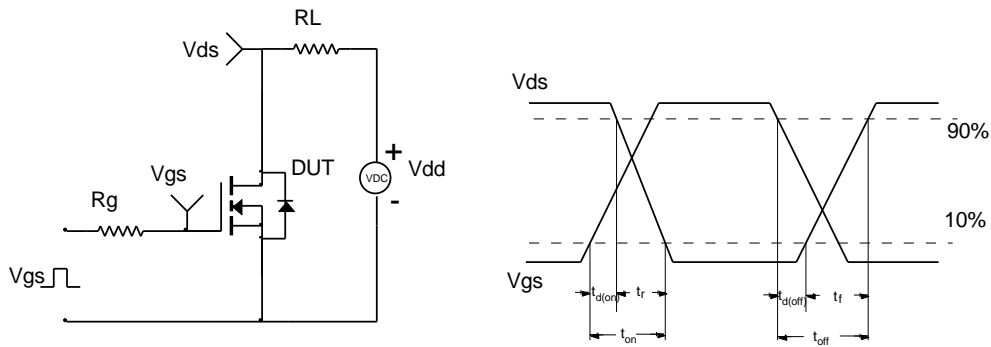


Test Circuit and Waveform

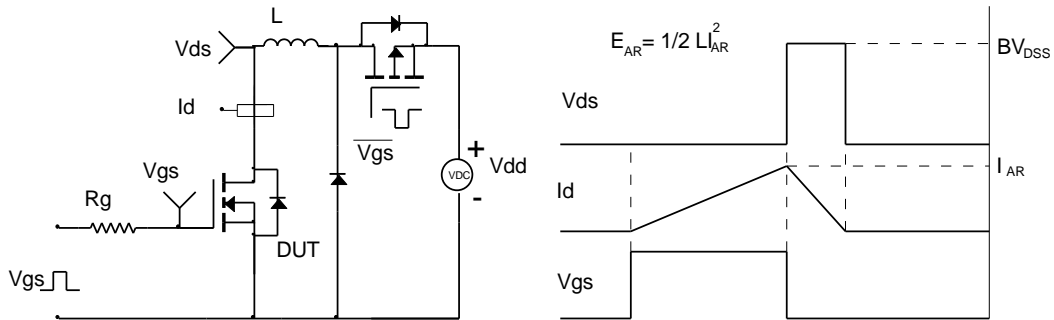
Gate Charge Test Circuit & Waveform



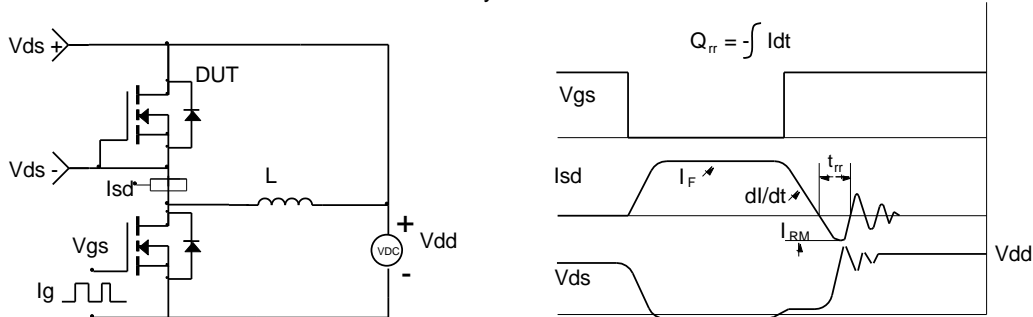
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



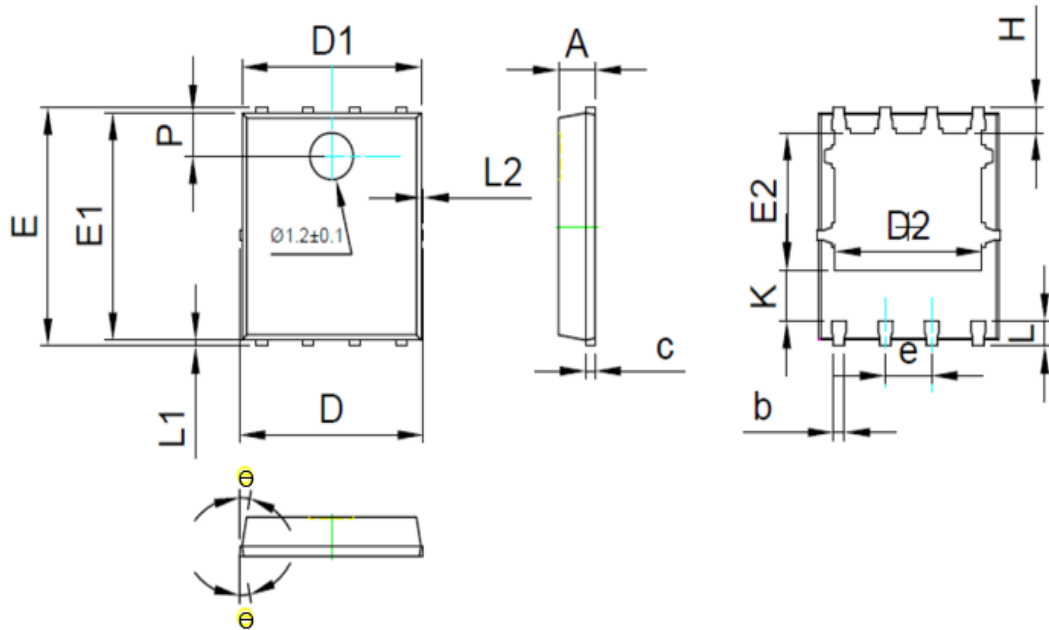
Diode Recovery Test Circuit & Waveforms



Package Outlines

Package Dimensions : PDFN 5*6 PACKAG

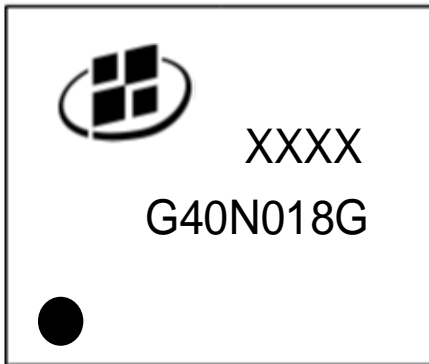
E



COMMON DIMENSIONS
(UNITS OF MEASURE = MILLIMETER)

| SYMBOL | MIN | NOM | MAX |
|----------|----------|-------|-------|
| A | 0.90 | 1.00 | 1.10 |
| b | 0.35 | 0.40 | 0.45 |
| c | 0.21 | 0.25 | 0.34 |
| D | - | - | 5.1 |
| D1 | 4.85 | 4.90 | 4.95 |
| D2 | 3.96 | 4.01 | 4.06 |
| e | 1.27 BSC | | |
| E | 5.95 | 6.00 | 6.05 |
| E1 | 5.70 | 5.75 | 5.80 |
| E2 | 3.425 | 3.475 | 3.525 |
| H | 0.60 | 0.65 | 0.70 |
| K | 1.29 | - | - |
| L | 0.60 | 0.65 | 0.70 |
| L1 | 0.05 | 0.15 | 0.25 |
| L2 | - | - | 0.12 |
| θ | 8° | 10° | 12° |
| P | 1.05 | 1.10 | 1.15 |

Marking Information



Note:

G40N018G = Product Name Code

XXXX = Date code

Contact ALKAIDSEMI sales for detail information

Tape & Reel Information

REEL DIMENSIONS

D1

TAPE DIMENSIONS

Pin 1 Cavity

A0: Dimension designed to accommodate the component width
 B0: Dimension designed to accommodate the component length
 K0: Dimension designed to accommodate the component thickness
 W: Overall width of the carrier tape
 P0: Pitch between successive cavity centers and sprocket hole
 P1: Pitch between successive cavity centers
 P2: Pitch between sprocket hole
 T: Tape material thickness
 D1: Reel Diameter
 W1: Reel Width

| DIMENSIONS | | | | | | | | | | (Unit: mm) | |
|------------|----|----|----|----|-----|-----|-----|------|----------------|------------|------|
| Reel | D1 | W1 | | | | | | | | Material | Hips |
| | P0 | P1 | P2 | W | A0 | B0 | K0 | T | Pin 1 Quadrant | Material | PC |
| Tape | 4 | 8 | 2 | 12 | 6.3 | 5.3 | 1.2 | 0.25 | Q1 | | |

All dimensions are nominal

Revision History

| Revision | Release Date | Remark |
|----------|--------------|--------|
| Rev.1.1 | 2022/4/20 | |

Disclaimer

The information given in this document describes the independent performance of the product, but similar performance is not guaranteed under other working conditions, and cannot be guaranteed when installed with other products or equipment. To achieve the required performance of the product in actual scenarios, the customer should conduct a complete application test to assess the functionality of the product.

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